

UTC UNISONIC TECHNOLOGIES CO., LTD

13003DF

Preliminary

NPN SILICON BIPOLAR TRANSISTORS FOR LOW FREQUENCY AMPLIFICATION

DESCRIPTION

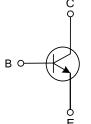
The UTC 13003DF is a silicon NPN power switching transistor; it uses UTC's advanced technology to provide customers high collector-base breakdown voltage, low reverse leakage current and high reliability, etc.

The UTC 13003DF is suitable for electronic ballast power switch circuit and the compact electronic energy-saving light.

FEATURES

- * High collector-base breakdown voltage
- * Low reverse leakage current
- * High reliability

EQUIVALENT CIRCUIT



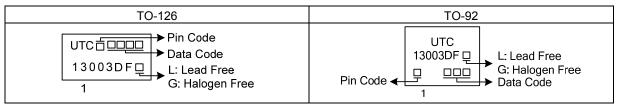
ORDERING INFORMATION

Ordering Number		Deekege	Pin Assignment			Dealving	
Lead Free	Halogen Free	Package	1	2	3	Packing	
13003DFL-xx-T60-F-K	13003DFG-xx-T60-F-K	-К ТО-126 В С Е		Bulk			
13003DFL-xx-T92-A-B	13003DFG-xx-T92-A-B	TO-92	Е	С	В	Tape Box	
13003DFL-xx-T92-A-K	13003DFG-xx-T92-A-K	13003DFG-xx-T92-A-K TO-92 E		С	В	Bulk	
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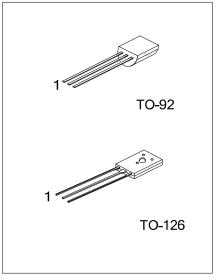
Note: Pin Assignment: B: Base C: Collector E: Emitter

13003DF <u>Ļ-Т60</u> - <u></u> Ę- <u></u> ₽	
(1)Packing Type	1) B: Bluk, K: Bulk
(2)Pin Assignment	2) refer to Pin Assignment
(3)Package Type	3) T60: TO-126, T92: TO-92
(4)Lead Free (4	4) L: Lead Free, G: Halogen Free

MARKING







■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise noted)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V _{CBO}	600	V
Collector-Emitter Voltage		V _{CEO}	400	V
Emitter-Base Voltage		V _{EBO}	9	V
Continuous Collector Current		Ι _C	1.5	A
Power Dissipation	T _A =25°C	D	1.25	W
	T _C =25°C	P _D	50	W
Junction Temperature		TJ	150	°C
Storage Temperature Range		T _{STG}	-55~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

ELECTRICAL CHARACTERISTICS (T_A = 25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =0.1mA	600			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =1mA	400			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I _E =0.1mA	9			V
Collector Cut-Off Current	I _{CBO}	V _{CB} =600V, I _E =0			0.1	mA
Collector-Emitter Cut-Off Current	I _{CEO}	V _{CE} =400V, I _B =0			0.1	mA
Emitter-Base Cut-Off Current	I _{EBO}	V _{EB} =9V, I _C =0			0.1	mA
DC Current Gain (Note 1)	h _{FE}	V _{CE} =5V, I _C =0.2A	15		30	
	b / b	h _{FE1} : V _{CE} =5V, I _C =5mA	0.75	0.9		
Low current and high current h _{FE2} h _{FE1} ratio	h _{FE1} / h _{FE2}	h _{FE2} : V _{CE} =5V, I _C =0.2A				
Collector-Emitter Saturation Voltage (Note)	V _{CE(SAT)}	I _C =1A, I _B =0.25A		0.3	0.9	V
Base-Emitter Saturation Voltage (Note)	V _{BE(SAT)}	I _C =1A, I _B =0.25A		0.9	1.2	V
Storage Time	ts		3		5	μs
Rise Time	t _R	UI9600, I _C =0.1A			1	μs
Fall Time	t _F				1	μs
Transition Frequency	f⊤	I _C =0.1A, V _{CE} =10V, f=1MHz	5			MHz

Note: Pulse test, pulse width tp≤300µs, Duty cycle≤2%

■ CLASSIFICATION OF h_{FE}

RANK	А	В	С
RANGE	15 ~ 20	20 ~ 25	25 ~ 30



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